PROCEEDINGS OF SPIE

Extreme Ultraviolet (EUV) Lithography VIII

Eric M. Panning
Kenneth A. Goldberg
Editors

27 February – 2 March 2017
San Jose, California, United States

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Published by
SPIE

Volume 10143

Proceedings of SPIE 0277-786X, V. 10143

SPIE is an international society advancing an interdisciplinary approach to the science and application of light.

Extreme Ultraviolet (EUV) Lithography VIII, edited by Eric M. Panning, Kenneth A. Goldberg, Proc. of SPIE
Vol. 10143, 1014301 · © 2017 SPIE · CCC code: 0277-786X/17/$18 · doi: 10.1117/12.2279234

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Please use the following format to cite material from these proceedings:
Author(s), "Title of Paper," in *Extreme Ultraviolet (EUV) Lithography VIII*, edited by Eric M. Panning, Kenneth A. Goldberg, Proceedings of SPIE Vol. 10143 (SPIE, Bellingham, WA, 2017) Seven-digit Article CID Number.

ISSN: 0277-786X
ISSN: 1996-756X (electronic)

ISBN: 9781510607378
ISBN: 9781510607385 (electronic)

Published by
SPIE
P.O. Box 10, Bellingham, Washington 98227-0010 USA
Telephone +1 360 676 3290 (Pacific Time) · Fax +1 360 647 1445
SPIE.org

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Session Chairs

1 Keynote Session
Eric M. Panning, Intel Corporation (United States)
Kenneth A. Goldberg, Lawrence Berkeley National Laboratory (United States)

2 EUV Materials I: Metal-Based EUV Resists: Joint Session with Conferences 10146 and 10143
Thomas I. Wallow, ASML Brion (United States)
Robert L. Brainard, SUNY CNSE/SUNYIT (United States)

3 EUV Materials II: Fundamentals I: Joint Session with Conferences 10146 and 10143
Clifford L. Henderson, Georgia Institute of Technology (United States)
Anna Lio, Intel Corporation (United States)

4 Tutorial Session: Joint Session with Conferences 10143 and 10146
Eric M. Panning, Intel Corporation (United States)
Kenneth A. Goldberg, Lawrence Berkeley National Laboratory (United States)

5 Integration
Jos P. Benschop, ASML Netherlands B.V. (Netherlands)
Daniel A. Corliss, IBM Corporation (United States)

6 EUV Mask Inspection and Imaging: Joint Session with Conferences 10143 and 10145
Anna Tchikoulaeva, Lasertec U.S.A., Inc. Zweigniederlassung Deutschland (Germany)
Ofer Adan, Applied Materials, Ltd. (Israel)

7 EUV Optics and Pellicle
Patrick P. Naulleau, Lawrence Berkeley National Laboratory (United States)
Yasin Ekinci, Paul Scherrer Institut (Switzerland)

9 Resist Advances and Integration
Robert Bristol, Intel Corporation (United States)
Nelson M. Felix, IBM Corporation (United States)

10 Resist Modeling
Thomas I. Wallow, ASML Brion (United States)
Christopher S. Ngai, Applied Materials, Inc. (United States)

11 Masks I
Emily E. Gallagher, IMEC (Belgium)
Obert R. Wood II, GLOBALFOUNDRIES Inc. (United States)

12 Masks II
Malahat Tarassasoli, Intel Corporation (United States)
Naoya Hayashi, Dai Nippon Printing Company, Ltd. (Japan)

13 Patterning I
Soichi Inoue, Toshiba Corporation (Japan)
Bryan S. Kasprowicz, Photronics, Inc. (United States)

14 Patterning II
Martin Burkhardt, IBM Thomas J. Watson Research Center (United States)
Thomas Scherise, Carl Zeiss SMT GmbH (Germany)

15 Source
Akiyoshi Suzuki, Gigaphoton Inc. (Japan)
Jos P. Benschop, ASML (United States)